General Purpose Transistor

PNP Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	-40	Vdc
Collector - Base Voltage	V _{CBO}	-40	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	Ic	-200	mAdc
Collector Current – Peak (Note 3)	I _{CM}	-800	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @ T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) @ T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-65 to +150	°C

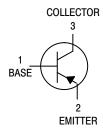
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.
- 3. Reference SOA curve.



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SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



2A = Specific Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

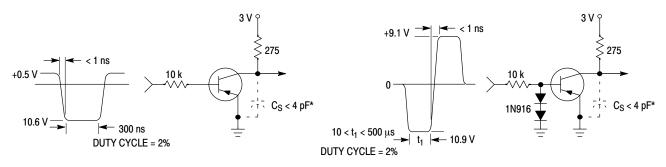
Device	Package	Shipping [†]
MMBT3906LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT3906LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBT3906LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBT3906LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Charac	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS		•			
Collector – Emitter Breakdown Voltage $(I_C = -1.0 \text{ mAdc}, I_B = 0)$			-40	_	Vdc
Collector – Base Breakdown Voltage ($I_C = -10 \mu Adc, I_E = 0$)		V _{(BR)CBO}	-40	_	Vdc
Emitter – Base Breakdown Voltage $(I_E = -10 \mu Adc, I_C = 0)$		V _{(BR)EBO}	-5.0	_	Vdc
Base Cutoff Current ($V_{CE} = -30 \text{ Vdc}$, $V_{EB} = -3.0 \text{ Vdc}$)		I _{BL}	-	-50	nAdc
Collector Cutoff Current (V _{CE} = -30 Vdc, V _{EB} = -3.0 Vdc)		I _{CEX}	_	-50	nAdc
ON CHARACTERISTICS (Note 4)		•			
DC Current Gain		H _{FE}	60 80 100 60 30	- 300 - -	_
Collector – Emitter Saturation Voltage ($I_C = -10 \text{ mAdc}$, $I_B = -1.0 \text{ mAdc}$) ($I_C = -50 \text{ mAdc}$, $I_B = -5.0 \text{ mAdc}$)	V _{CE(sat)}	_ _	-0.25 -0.4	Vdc	
Base-Emitter Saturation Voltage ($I_C = -10$ mAdc, $I_B = -1.0$ mAdc) ($I_C = -50$ mAdc, $I_B = -5.0$ mAdc)	V _{BE(sat)}	-0.65 -	-0.85 -0.95	Vdc	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain - Bandwidth Product ($I_C = -10 \text{ mAdc}, V_{CE} = -20 \text{ Vdc}, f$	= 100 MHz)	f _T	250	-	MHz
Output Capacitance $(V_{CB} = -5.0 \text{ Vdc}, I_E = 0, f = 1.0 \text{ M})$	C _{obo}	-	4.5	pF	
Input Capacitance ($V_{EB} = -0.5 \text{ Vdc}$, $I_C = 0$, $f = 1.0 \text{ M}$	Hz)	C _{ibo}	-	10	pF
Input Impedance ($I_C = -1.0 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$,	f = 1.0 kHz)	h _{ie}	2.0	12	kΩ
Voltage Feedback Ratio ($I_C = -1.0 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$,	f = 1.0 kHz)	h _{re}	0.1	10	X 10 ⁻⁴
Small – Signal Current Gain ($I_C = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc},$	h _{fe}	100	400	-	
Output Admittance ($I_C = -1.0 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$,	h _{oe}	3.0	60	μmhos	
Noise Figure (I _C = $-100 \mu Adc$, V _{CE} = $-5.0 Vdc$,	NF	-	4.0	dB	
SWITCHING CHARACTERISTICS		•	•	•	•
Delay Time	$(V_{CC} = -3.0 \text{ Vdc}, V_{BE} = 0.5 \text{ Vdc},$	t _d	_	35	no
Rise Time	$I_C = -10 \text{ mAdc}, I_{B1} = -1.0 \text{ mAdc})$	t _r	-	35	ns
Storage Time	$(V_{CC} = -3.0 \text{ Vdc}, I_{C} = -10 \text{ mAdc},$	t _s	_	225	ns
Fall Time	$I_{B1} = I_{B2} = -1.0 \text{ mAdc}$			75	113

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different and the end of t performance may not be indicated by the Electrical Characteristics if operated under different conditions. 4. Pulse Test: Pulse Width $\leq 300~\mu s$, Duty Cycle $\leq 2.0\%$.

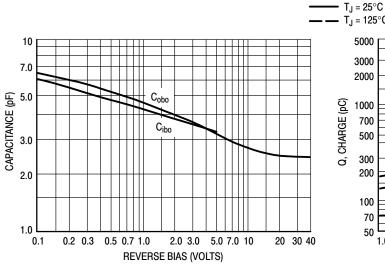


* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time **Equivalent Test Circuit**

Figure 2. Storage and Fall Time **Equivalent Test Circuit**

TYPICAL TRANSIENT CHARACTERISTICS





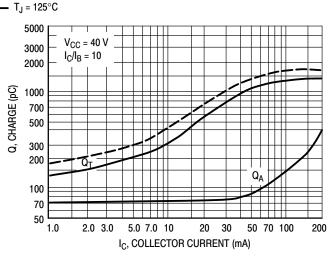
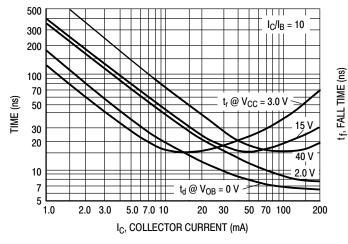


Figure 4. Charge Data





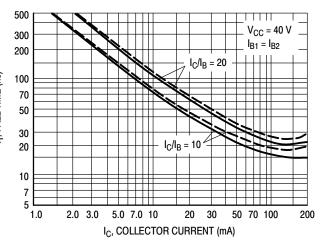
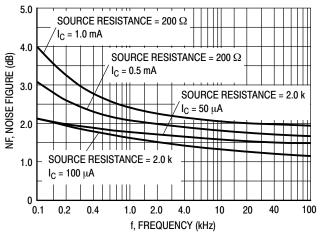


Figure 6. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = -5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$



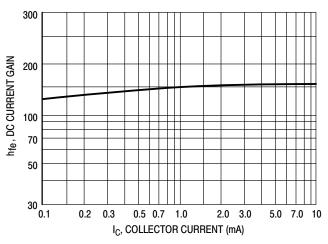
12 f = 1.0 kHz10 NF, NOISE FIGURE (dB) 8 6 4 $I_C = 50 \mu A$ I_C = 100 μA 0.2 40 100 0.4 0.1 1.0 2.0 4.0 20 R_g, SOURCE RESISTANCE (k OHMS)

Figure 7.

Figure 8.

h PARAMETERS

 $(V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz}, T_A = 25^{\circ}\text{C})$



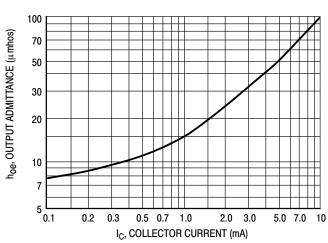
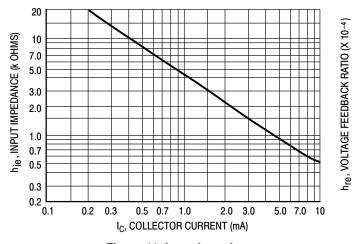


Figure 9. Current Gain

Figure 10. Output Admittance



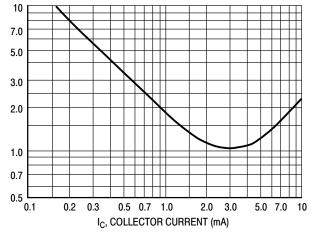


Figure 11. Input Impedance

Figure 12. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

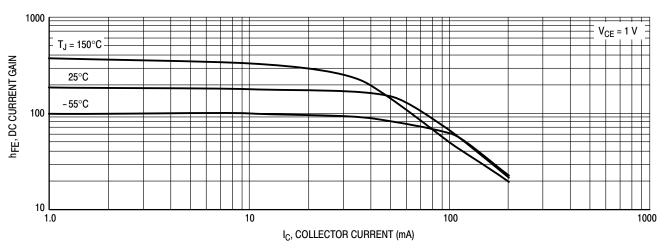


Figure 13. DC Current Gain

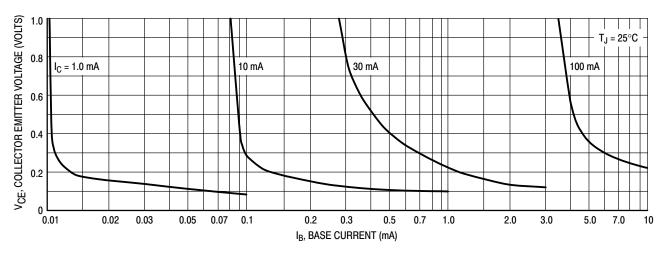


Figure 14. Collector Saturation Region

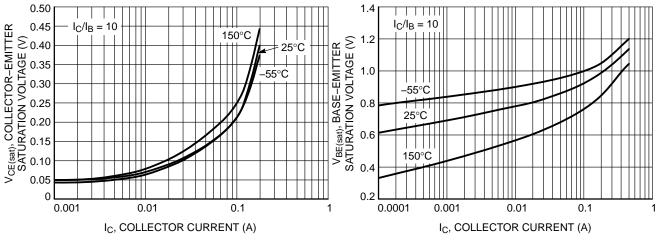


Figure 15. Collector Emitter Saturation Voltage vs. Collector Current

Figure 16. Base Emitter Saturation Voltage vs. **Collector Current**

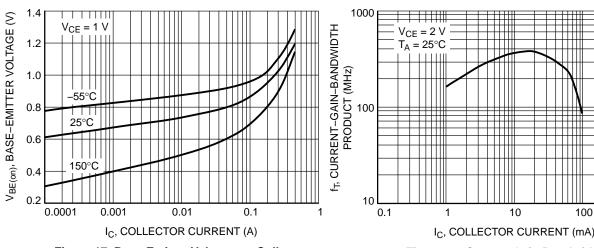


Figure 17. Base Emitter Voltage vs. Collector Current

Figure 18. Current Gain Bandwidth vs. **Collector Current**

100

1000

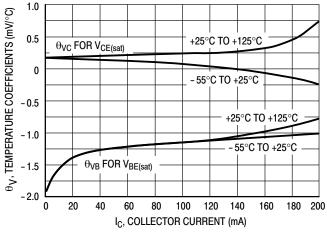


Figure 19. Temperature Coefficients

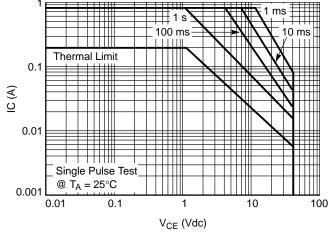


Figure 20. Safe Operating Area

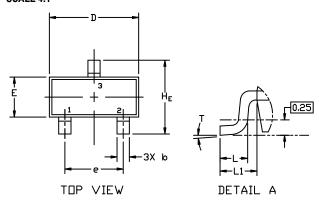


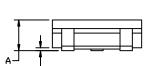


SOT-23 (TO-236) **CASE 318 ISSUE AT**

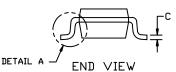
DATE 01 MAR 2023

SCALE 4:1





SIDE VIEW



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIM	IETERS		INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

GENERIC MARKING DIAGRAM*

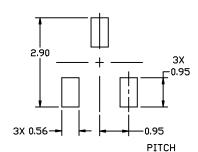


XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9:	STYLE 10:	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN		PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE		2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE		3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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